

ABSTRACT OF THE DISCLOSURE

Gates of pMISFETs which need high current driving capability are high-driving-capability gates placed in discontinuous active regions or high-driving-capability gates disposed in two-input active regions. Gate of pMISFETs which do not need high current driving capability are normal gates arranged in continuous active regions. Since the high-driving-capability gates are provided in the discontinuous active regions or the two-input active regions, pMISFETs with high driving capability is achieved by utilizing light holes created due to a lattice distortion.